

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED
- U.L. RECOGNISED ISOWATT218 PACKAGE (U.L. FILE # E81734 (N))

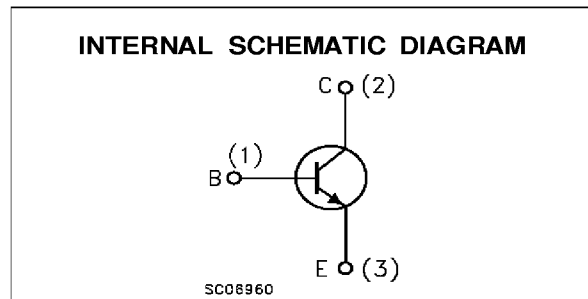
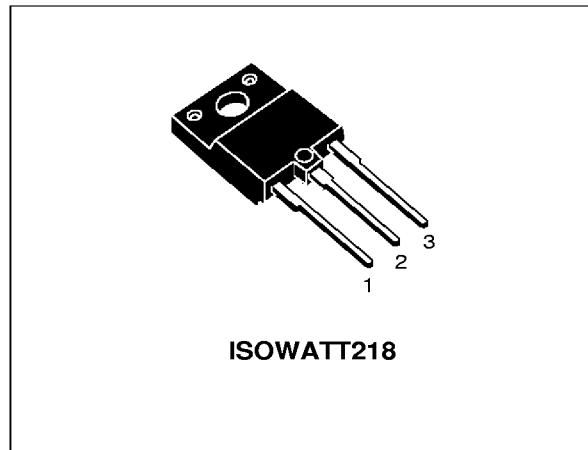
APPLICATIONS:

- HORIZONTAL DEFLECTION FOR MONITORS

DESCRIPTION

The THD200FI is manufactured using Multi-epitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.

The THD series is designed for use in horizontal deflection circuits in televisions and monitors.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	1500	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	700	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	10	V
I_C	Collector Current	10	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	20	A
I_B	Base Current	5	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	10	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	57	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THD200FI

THERMAL DATA

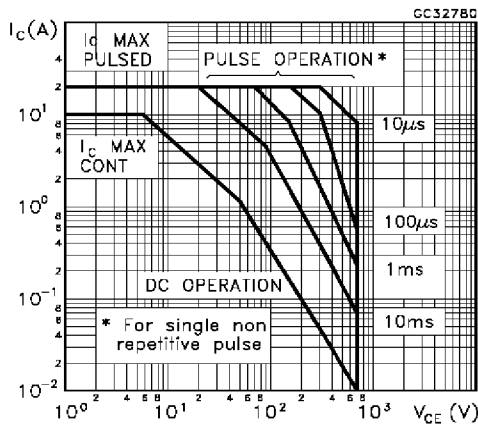
$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.2	$^{\circ}C/W$
----------------	----------------------------------	-----	-----	---------------

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

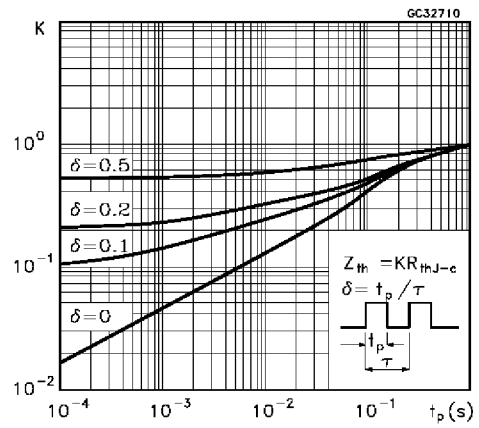
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 1500 V$ $V_{CE} = 1500 V \quad T_j = 125^{\circ}C$			0.2 2	mA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5 V$			100	μA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 100 mA$	700			V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	$I_E = 10 mA$	10			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 7 A \quad I_B = 1.5 A$			1.5	V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 7 A \quad I_B = 1.5 A$			1.3	V
h_{FE*}	DC Current Gain	$I_C = 7 A \quad V_{CE} = 5 V$ $I_C = 7 A \quad V_{CE} = 5 V \quad T_j = 100^{\circ}C$	6.5 4		13	
t_s t_f	RESISTIVE LOAD Storage Time Fall Time	$V_{CC} = 400 V \quad I_C = 7 A$ $I_{B1} = 1.5 A \quad I_{B2} = 3.5 A$		2.1 140	3.1 210	μs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 7 A \quad f = 31250 Hz$ $I_{B1} = 1.5 A \quad I_{B2} = -3.5 A$ $V_{ceflyback} = 1200 \sin\left(\frac{\pi}{5} 10^6\right) t \quad V$		3.5 320		μs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 7 A \quad f = 64 KHz$ $I_{B1} = 1.5 A \quad I_{B2} = -3.5 A$ $V_{ceflyback} = 1200 \sin\left(\frac{\pi}{5} 10^6\right) t \quad V$		1.7 215		μs ns

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

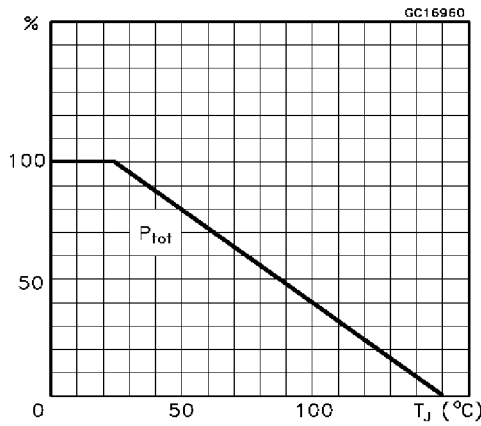
Safe Operating Area Derating Curve



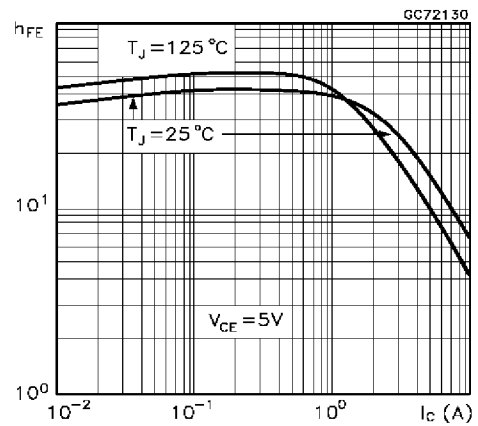
Thermal Impedance



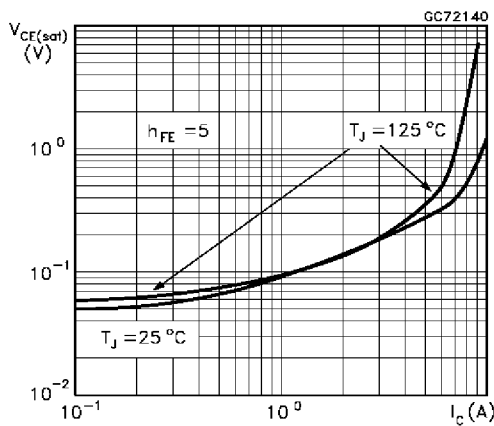
Derating Curve



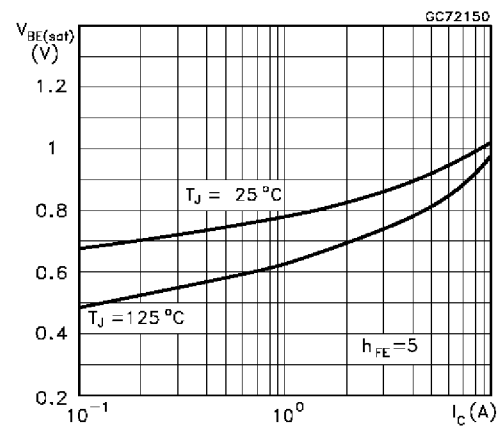
DC Current Gain



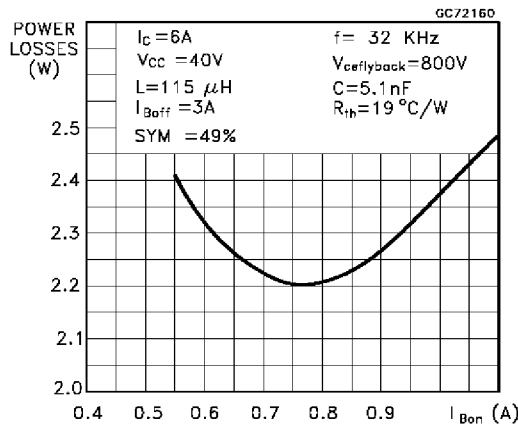
Collector Emitter Saturation Voltage



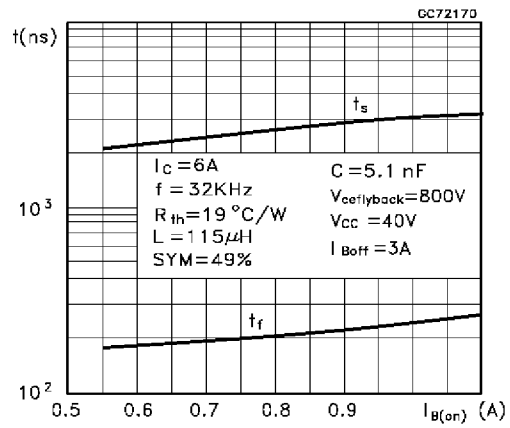
Base Emitter Saturation Voltage



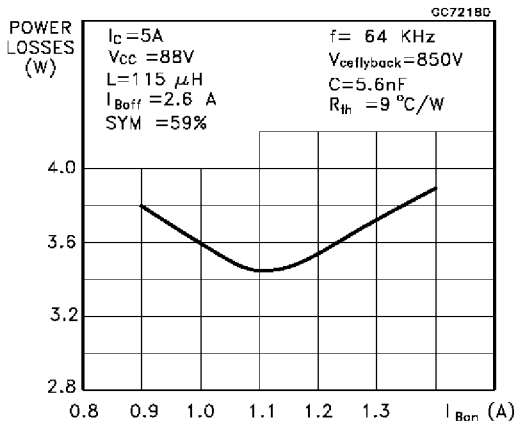
Power Losses at 32 KHz



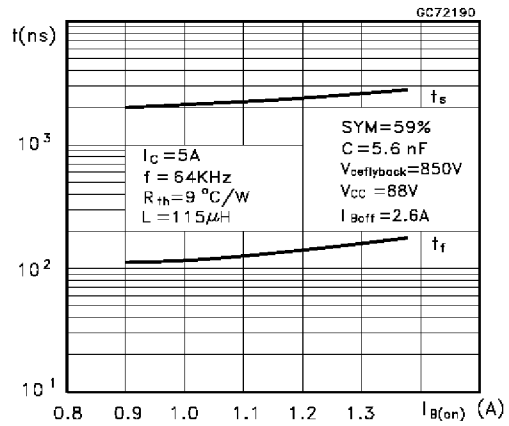
Switching Time Inductive Load at 32 KHz (see figure 2)



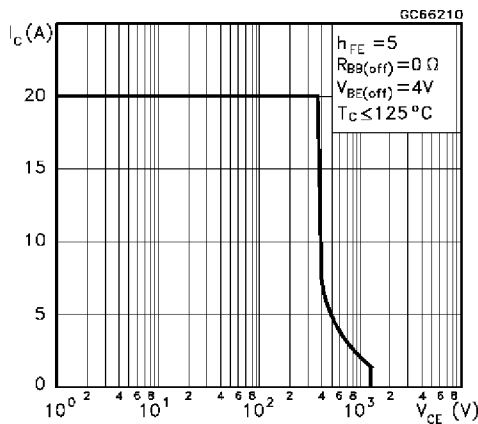
Power Losses at 64 KHz



Switching Time Inductive Load at 64 KHz (see figure 2)



Reverse Biased SOA



BASE DRIVE INFORMATION

In order to saturate the power switch and reduce conduction losses, adequate direct base current I_{B1} has to be provided for the lowest gain h_{FE} at $T_j = 100\text{ }^\circ\text{C}$ (line scan phase). On the other hand, negative base current I_{B2} must be provided turn off the power transistor (retrace phase). Most of the dissipation, especially in the deflection application, occurs at switch-off so it is essential to determine the value of I_{B2} which minimizes power losses, fall time t_f and, consequently, T_j . A new set of curves have been defined to give total power losses, t_s and t_f as a function of I_{B2} at both 32 KHz and 64 KHz scanning frequencies in order to choose the optimum negative drive. The test circuit is illustrated in fig. 1.

Inductance L_1 serves to control the slope of the negative base current I_{B2} in order to recombine the excess carriers in the collector when base current is still present, thus avoiding any tailing phenomenon in the collector current.

The values of L and C are calculated from the following equations:

$$\frac{1}{2} L (I_c)^2 = \frac{1}{2} C (V_{CEfly})^2$$

$$\omega = 2 \pi f = \frac{1}{\sqrt{LC}}$$

Where I_c = operating collector current, V_{CEfly} = flyback voltage, f = frequency of oscillation during retrace.

Figure 1: Inductive Load Switching Test Circuit.

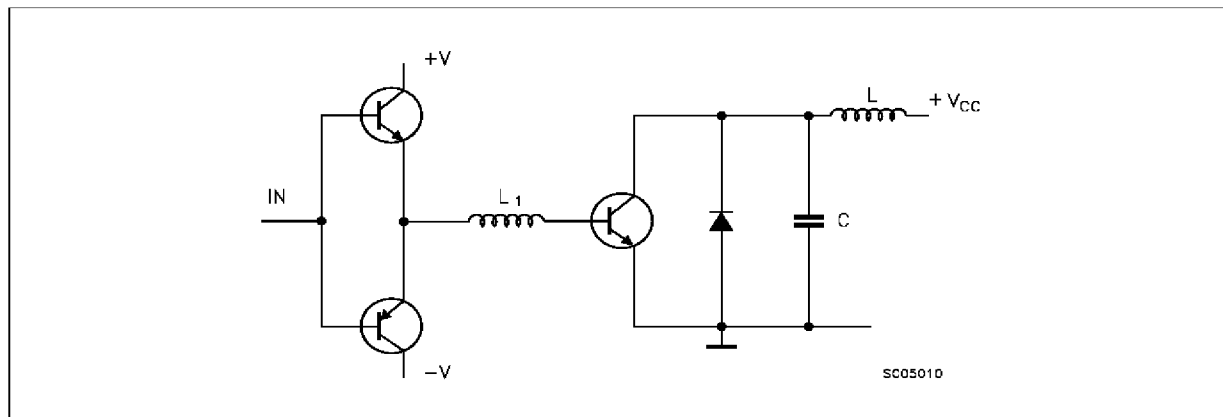
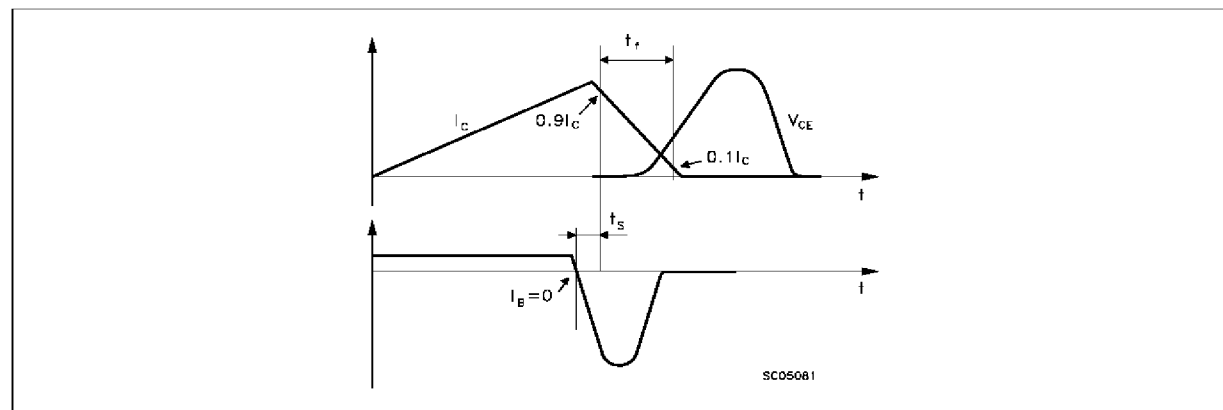


Figure 2: Switching Waveforms in a Deflection Circuit.



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	

